## 3/4 B.Tech - SIXTH SEMESTER

EC 6T1 VLSI Design Credits: 4

Lecture : 4 periods/week Internal assessment: 30 marks
Tutorial: 1 period /week Semester end examination: 70 marks

# **Course Objectives:**

- Understand VLSI Design Flow
- Learn Transistor-Level CMOS Logic Design
- Understand VLSI Fabrication
- Learn to Analyze Gate Function and Timing Characteristics

# **Learning Outcomes:**

- Gain knowledge of different VLSI fabrication processes and CMOS Logic Design.
- Design different MOS logical circuits.
- Understand the effects of Scaling.
- Understand the programmable architectures such as, PLDs, CPLDs and FPGAs.

## UNIT-I

**Introduction**: Introduction to IC Technology, The IC Era, MOS and related VLSI Technology, Basic MOS Transistors. Enhancement and Depletion modes of transistor action, MOS and CMOS Fabrication process, BiCMOS Technology, Comparison between CMOS and Bipolar technologies.

## **UNIT-II**

Basic Electrical Properties of MOS and Bi CMOS Circuits: Id versus Vds Relationships, Aspects of MOS transistor Threshold Voltage, MOS transistor Trans-conductance and Output Conductance, MOS transistor Figure of Merit, The Pass transistor. The nMOS Inverter, Determination of Pull-up to Pull-Down Ratio for nMOS inverter driven by another nMOS inverter and for an nMOS inverter driven through one or more pass transistors, Alternative forms of pull-up, The CMOS Inverter, MOS transistor circuit model, Bi-CMOS Inverter, Latch-up in CMOS circuits and BiCMOS Latch-up Susceptibility.

#### **UNIT-III**

MOS and BiCMOS Circuit Design Processes: MOS Layers, Stick Diagrams, Design Rules and Layout, General observations on the Design rules, Layout Diagrams of NAND, NOR gates, CMOS inverter and different logic functions.

## **UNIT-IV**

**Basic Circuit Concepts:** Sheet Resistance, Sheet Resistance concept applied to MOS transistors and Inverters, Area Capacitance of Layers, Standard unit of capacitance, Some area Capacitance Calculations, The Delay Unit Inverter Delays, Driving large capacitive loads, Propagation Delays, Wiling Capacitances, Fan-in and fan-out characteristics, Choice of layers, Transistor switches, Realization of gates using nMOS, pMOS and CMOS technologies.

#### **UNIT-V**

**Scaling of MOS Circuits:** Scaling models and scaling factors, Scaling factors for device parameters, Limitations of scaling, Limits due to sub threshold currents, Limits on logic levels and supply voltage due to noise, Limits due to current density, Introduction to Switch Logic and Gate Logic.

## **UNIT-VI**

**Semiconductor Integrated Circuit Design:** Introduction to Programmable Logic Devices (PLDs), Programmable Logic Arrays (PLA), Programmable Array Logic (PAL). Implementation approaches in VLS1 Design-full Custom Design, Semicustom Design, Gate Arrays, and Standard Cells.

## **UNIT-VII**

**Field Programmable Gate Arrays and Complex Programmable Logic Devices:** Xilinx 3000 Series FPGAs, Xilinx 4000 Series FPGAs, Using a One-Hot State Assignment, Altera Complex Programmable Logic Devices (CPLDs), Altera FLEX 10K Series CPLDs.

## **UNIT-VIII**

**Test Principles :** Need for testing, Test Principles, Design Strategies for test, Chip level Test Techniques, System-level Test Techniques, Layout Design for improved Testability.

# **Learning Resources**

#### **Text Books:**

- 1. Essentials of VLSI Circuits and Systems- Kamran Eshraghian, Douglas and A Pucknell, PHI. Private Limited, 2005.
- 2 Principles of CMOS VLSI Design Weste and Eshraghian, Pearson Education, 1999.

## **References:**

- 1. Chip Design for Submicron VLSI: CMOS Layout & Simulation, John P. Uyemura, Thomson Learning, 2005.
- 2. Introduction to VLSI Circuits and Systems John .P. Uyemura, JohnWiley, 2003.
- 3. Digital Integrated Circuits John M. Rabaey, PHI, EEE, 1997.
- 4. Modern VLSI Design Wayne Wolf, Pearson Education, 3rd Edition, 1997.
- 5. VLSI Technology S.M. SZE, 2nd Edition, TMH, 2003.
- 6. Fundamentals of Logic Design with VHDL- Stephen. Brown and ZvonkoVranesic, TMH, 2005